

## EAST Search History (Prior Art)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	1	10/594742.app.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/01/06 13:46
S2	6	("6,620,641" "6,649,942" "20010004112" "20030062531" "20040079955" "6,335,546").pn.	US-PGPUB; USPAT	OR	ON	2010/01/06 15:25
S5	3	(elo epitaxial near1 lateral near1 (growth overgrowth)) same (layer film region) same gap near2 substrate same active near1 (layer region film)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/01/06 17:53
S6	22	(elo epitaxial near1 lateral near1 (growth overgrowth)) same (layer film region) same active near1 (layer region film) and gap near2 substrate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/01/06 17:54
S7	8	("20010004112" "20030062531" "20040079955" "6335546" "6335549" "6620641" "6649942" "6995406").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2010/03/27 23:12
S13	11228	active near1 (layer region) near10 p-type near1 layer near10 n-type near1 layer	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/27 23:21
S12	3463	active near1 (layer region) same p-type near1 layer same n-type near1 layer	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/27 23:21
S15	2256	(light near1 emi\$5 near1 (diode device) LED) same active near1 (layer region) near5 p-type near1 layer near5 n-type near1 layer	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/27 23:22

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S14	6516	active near1 (layer region) near5 p-type near1 layer near5 n-type near1 layer	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/27 23:22
S16	813	(light near1 emi\$5 near1 (diode device) LED) near10 active near1 (layer region) near5 p-type near1 layer near5 n-type near1 layer	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/27 23:23
S18	1035	active near1 (layer region) near10 p-type near1 (well barrier) near5 n-type near1 (well barrier)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/27 23:24
S17	147	(light near1 emi\$5 near1 (diode device) LED) near5 active near1 (layer region) near5 p-type near1 layer near5 n-type near1 layer	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/27 23:24
S20	5	active near1 (layer region) same (p-type near1 (well) near5 n-type near1 (barrier) p-type near1 (barrier) near5 n-type near1 (well))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/27 23:26
S21	12	active near1 (layer region) same (p-type near1 (well) near10 n-type near1 (barrier) p-type near1 (barrier) near10 n-type near1 (well))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/27 23:27
S22	27	(light near1 emi\$5 near1 (diode device) LED) same modulation near5 dop\$5 near10 (emis\$5 active) near1 (layer region)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/27 23:48

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S24	63	(light near1 emi\$5 near1 (diode device) LED) and modulation near5 dop\$5 near10 (emis\$5 active) near1 (layer region)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/28 00:05
S26	239	(elo elog lateral near1 (growth overgrowth) epitaxial near1 lateral near1 (growth overgrowth)) same (layer film region) and gap near5 substrate and buffer	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/05/18 16:17
S27	3	"11313515"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/05/19 19:58
S28	483	(257/13,94,103,e21.561-e21.566,e21.571-e21.573 438/481,413,416).ccls. and gap and (lateral near1 growth overgrowth over near1 growth elo)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/08/29 23:39
S29	310	(257/13,94,103,e21.561-e21.566,e21.571-e21.573 438/481,413,416).ccls. and gap and (lateral near1 growth overgrowth over near1 growth elo) and (window aperture opening)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/08/29 23:40
S31	124	(257/13,94,103,e21.561-e21.566,e21.571-e21.573 438/481,413,416).ccls. and gap near10 substrate and (lateral near1 growth overgrowth over near1 growth elo pendeo) and (window aperture opening)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/08/29 23:48
S30	124	(257/13,94,103,e21.561-e21.566,e21.571-e21.573 438/481,413,416).ccls. and gap near10 substrate and (lateral near1 growth overgrowth over near1 growth elo) and (window aperture opening)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/08/29 23:48

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S32	69	(257/13,94,103,e21.561-e21.566,e21.571-e21.573 438/481,413,416).ccls. and gap near10 substrate and (lateral near1 growth overgrowth over near1 growth elo pendeo) and (window aperture opening) and (Light near1 emi\$6 near1 (diode device element structure))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/08/29 23:52
S33	7	(257/13,94,103,e21.561-e21.566,e21.571-e21.573 438/481,413,416).ccls. and gap near10 substrate and (lateral near1 growth overgrowth over near1 growth elo pendeo) and (window aperture opening) and (Light near1 emi\$6 near1 (diode device element structure)) and liquid near1 phase near epitaxy	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/08/30 00:02

### EAST Search History (Interference)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S34	2	(257/13,94,103,e21.561-e21.566,e21.571-e21.573 438/481,413,416).ccls. and (gap near10 substrate and (lateral near1 growth overgrowth over near1 growth elo pendeo) and (window aperture opening) and (Light near1 emi\$6 near1 (diode device element structure))).clm.	US-PGPUB; USPAT; UPAD	OR	ON	2010/08/30 00:09